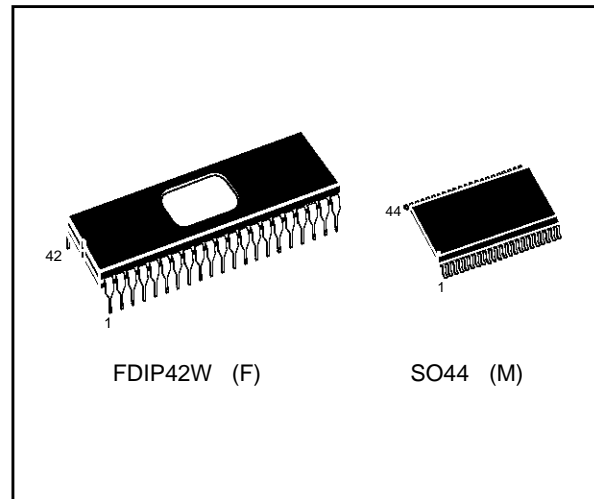


LOW VOLTAGE 8 Megabit (1Meg x 8 or 512K x 16) UV EPROM and OTP EPROM

DATA BRIEFING

- LOW VOLTAGE READ OPERATION:
3V to 5.5V
- FAST ACCESS TIME: 120ns
- WORD-WIDE or BYTE-WIDE
CONFIGURABLE
- 8 Megabit MASK ROM COMPATIBLE
- LOW POWER CONSUMPTION
 - Active Current 70mA at 8MHz
 - Standby Current 100µA
- PROGRAMMING VOLTAGE $12.5V \pm 0.3V$
- PROGRAMMING TIME of AROUND 26sec.
(PRESTO III ALGORITHM)
- M27V800 is PROGRAMMABLE as M27C800
with IDENTICAL SIGNATURE

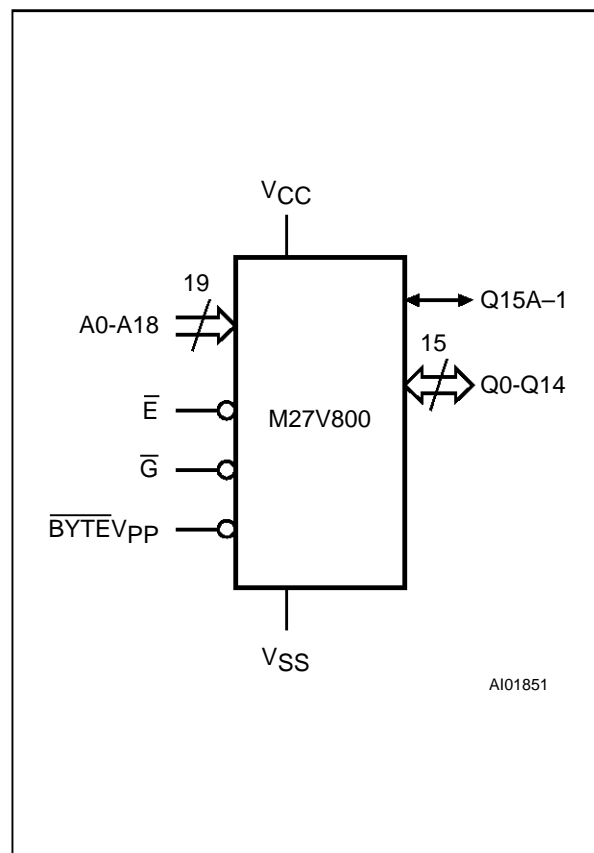


DESCRIPTION

The M27V800 is a low voltage, low power 8 Megabit UV erasable and electrically programmable EPROM ideally suited for microprocessor systems requiring large data or program storage. It is organised as either 1Meg words of 8 bit or 512K words of 16 bit. The pin-out is compatible with a 8 Megabit Mask ROM.

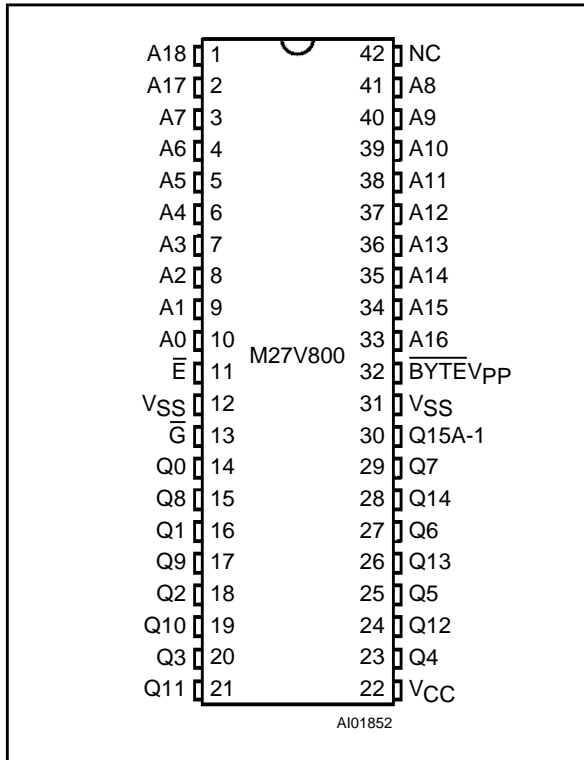
The M27V800 operates in the read mode with a supply voltage as low as 3V. The decrease in operating power allows either a reduction of the size of the battery or an increase in the time between battery recharges.

Logic Diagram



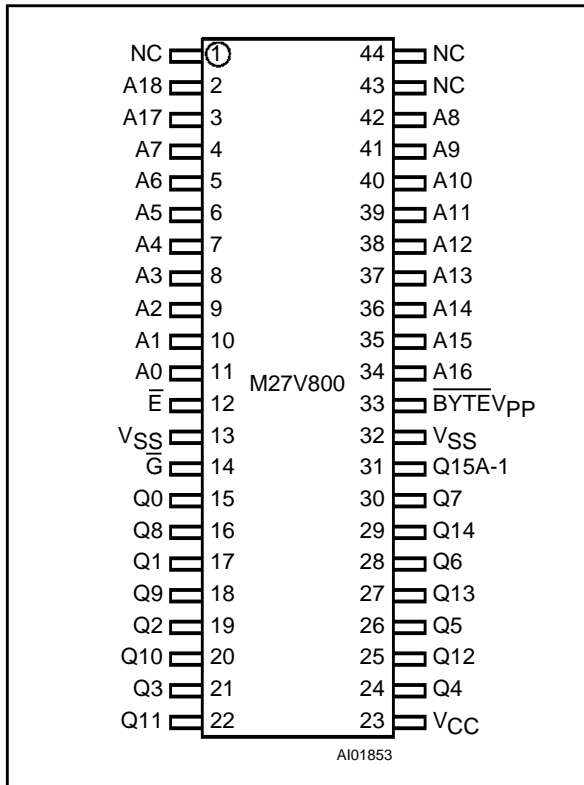
M27V800

DIP Pin Connections



Warning: NC = Not Connected

SO Pin Connections



Warning: NC = Not Connected

Signal Names

A0 - A18	Address Inputs
Q0 - Q7	Data Outputs
Q8 - Q14	Data Outputs
Q15A-1	Data Output / Address Input
\bar{E}	Chip Enable
\bar{G}	Output Enable
$\overline{BYTEV_{PP}}$	Byte Mode / Program Supply
V _{CC}	Supply Voltage
V _{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

Example: M27V800 -120 M 1

